



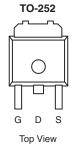
# P-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)	
- 60	0.060 at V <sub>GS</sub> = - 10 V	- 19	26	
- 60	0.077 at V <sub>GS</sub> = - 4.5 V	- 16.8	20	

#### **FEATURES**

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature

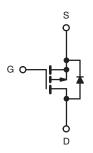




Drain Connected to Tab

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Ordering Information: SUD19P06-60L-E3 (Lead (Pb)-free)



P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	7 v	
Continuous Drain Current /T 175 °C\	T <sub>C</sub> = 25 °C	l <sub>D</sub>	- 19	Α	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 125 °C		- 11		
Pulsed Drain Current		I <sub>DM</sub>	- 30	А	
Avalanche Current, Single Pulse  L = 0.1 mH		I <sub>AS</sub>	- 22		
Repetitive Avalanche Energy, Single Pulse <sup>a</sup>		E <sub>AS</sub>	24.2	mJ	
Davier Discination	T <sub>C</sub> = 25 °C	· D	46 <sup>c</sup>	W	
Power Dissipation	T <sub>A</sub> = 25 °C		2.7 <sup>b, c</sup>	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
handing to Austrianth	t ≤ 10 s	- R <sub>thJA</sub>	17	21	°C/W
Junction-to-Ambient <sup>b</sup>	Steady State		45	55	
Junction-to-Case		R <sub>thJC</sub>	2.7	3.25	

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When monuted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	μΑ
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 ° C			- 150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 30			Α
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		0.048	0.060	Ω
Dunin Course On State Besistance	r ·	$V_{GS} = -10 \text{ V}, I_D = -16.8 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.102	
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, I_D = -16.8 \text{ A}, T_J = 175 ^{\circ}\text{C}$			0.129	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.061	0.077	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 10 A		22		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			1140	1710	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		130		
Reverse Transfer Capacitance	C <sub>rss</sub>			90		
Total Gate Charge	Qg			26	40	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ A}$		4.5		nC
Gate-Drain Charge	$Q_{gd}$			7.0		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		7.0		Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	15	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V}, R_{L} = 3 \Omega$		9	15	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 19 A, $V_{GEN}$ = - 10 V, $R_g$ = 2.5 $\Omega$		65	100	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		30	45	
Drain-Source Body Diode Characterist	ics (T <sub>C</sub> = 25 °C)	b			<u> </u>	
Continuous Current	I <sub>S</sub>				- 30	
Pulsed Current	I <sub>SM</sub>				- 30	Α
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 19 A, V <sub>GS</sub> = 0 V		- 1.0	- 1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 19 A, di/dt = 100 A/μs		41	61	ns

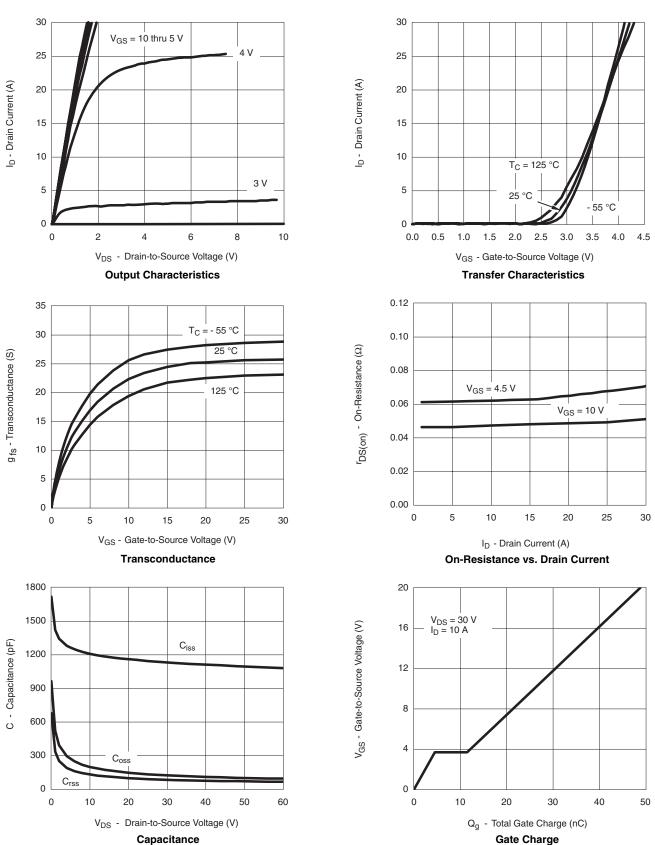
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



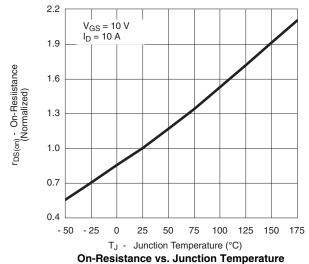
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

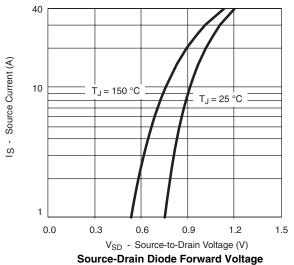


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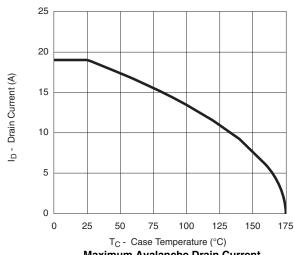
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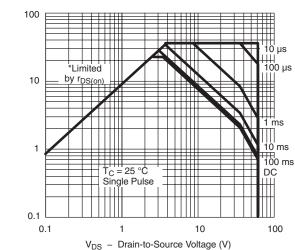
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



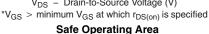


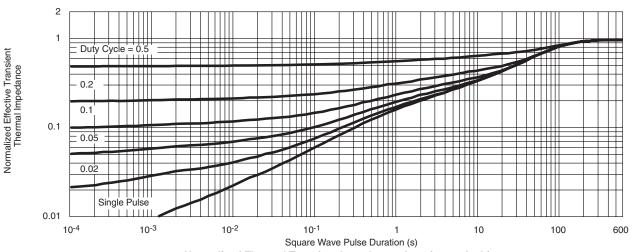
#### THERMAL RATINGS





Maximum Avalanche Drain Current vs. Case Temperature





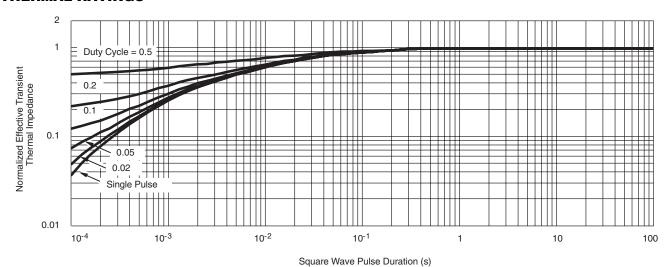
ID - Drain Current (A)

Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### THERMAL RATINGS



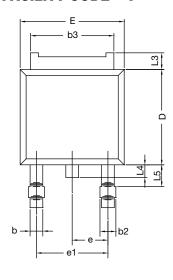
Normalized Thermal Transient Impedance, Junction-to-Case

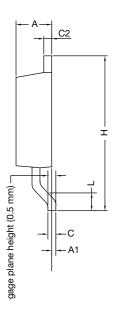
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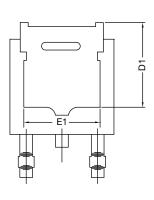


## **TO-252AA Case Outline**

#### **VERSION 1: FACILITY CODE = Y**







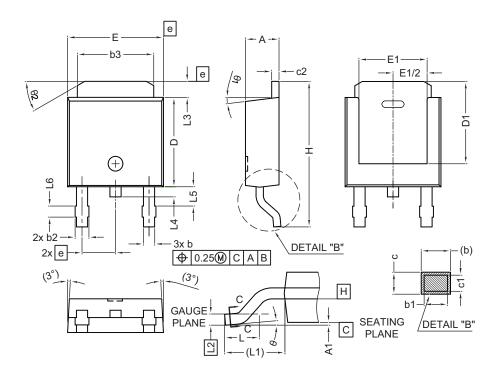
	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	=	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40 1.78		
L3	0.89 1.27		
L4	- 1.02		
L5	1.01	1.52	

#### Note

• Dimension L3 is for reference only



#### **VERSION 2: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
Е	6.35	6.73	
E1	4.32	-	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

#### Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022

DWG: 5347



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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